

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	190	361/41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/13 14:38
S2	14	"6,249,410"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 09:22
S3	22	("4855620" "4937700" "5086365" "5237395" "5255146" "5287241" "5311391" "5440162" "5500546" "5598313" "5610791" "5625280" "5631793" "5774318" "5784242" "5825603" "5835328" "5946175" "5956219" "5959488" "5959820" "6172383").PN.	USPAT	OR	ON	2004/09/01 13:29
S4	22	("4855620" "4937700" "5086365" "5237395" "5255146" "5287241" "5311391" "5440162" "5500546" "5598313" "5610791" "5625280" "5631793" "5774318" "5784242" "5825603" "5835328" "5946175" "5956219" "5959488" "5959820" "6172383").PN.	USPAT	OR	ON	2004/09/01 13:29
S5	24	"5,959,820"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 15:35
S6	814	esd same bipolar adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 15:36
S7	4	esd same bipolar adj transistor near (clamp clamping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 15:38
S8	17	"4,924,339"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 15:40

S9	30	"4,994,874"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 15:40
S10	15	"5,079,612"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 15:45
S11	4	"5,196,913"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 15:47
S12	46	"5,218,222"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 16:00
S13	23	"5,272,371"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 16:26
S14	766	361/91.1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 16:26
S15	0	esd same no adj power near active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 10:11
S16	0	esd and no adj power near active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 10:12
S17	0	esd and no adj power near (active conducting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 10:12
S18	0	esd and (no lack adj of) adj power near (active conducting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 10:13

S19	408	esd and power near applied	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 10:13
S20	288	esd and power adj applied	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 10:13
S21	0	esd and power adj applied near active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 10:14
S22	2	esd and power adj applied near (active conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 10:14
S23	2	esd and power adj applied near (enable enabled enabling)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 10:16
S24	0	esd and power adj applied near (enable enabled enabling) near esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 10:16
S25	0	esd and power adj (absent lack) near (enable enabled enabling)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 10:17
S26	0	esd and power adj (absent lack) near (operative operating)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 10:18
S27	0	esd same power adj (absent lack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 10:18
S28	58	esd same power adj applied	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 12:03

S29	33	esd and (programming program) adj circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 12:05
S30	66	esd and (programming program programmable) adj circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 12:06
S31	0	esd and (programming program programmable) adj circuit same power near applied	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 12:06
S32	0	esd and (programming program programmable) adj circuit same circuit adj assembled	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 12:06
S33	0	esd and (programming program programmable) adj circuit same circuit near assembled	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 12:07
S34	0	esd same (programming program programmable) adj circuit same circuit near assembled	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 12:08
S35	5	esd same (programming program programmable) adj circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 15:56
S36	7	("5287241" "5369552" "5784242" "5959821" "5970321" "5991135" "6060752").PN.	USPAT	OR	ON	2004/09/02 12:13
S37	4	("4446534" "4823320" "5663902" "6028756").PN.	USPAT	OR	ON	2004/09/02 12:52
S38	3	("4412241" "4823181" "5151611").PN.	USPAT	OR	ON	2004/09/02 16:10
S39	25	"5341267".URPN.	USPAT	OR	ON	2004/09/02 16:12
S40	3	("4412241" "4823181" "5151611").PN.	USPAT	OR	ON	2004/09/02 16:20
S41	3129	361/111	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 17:05

S42	36	esd and threshold near (programming programmed programmable)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 11:56
S43	2	esd same threshold near (programming programmed programmable)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 10:30
S44	3	("5173755" "5400202" "5717558").PN.	USPAT	OR	ON	2004/09/09 10:31
S45	1	"5995354".URPN.	USPAT	OR	ON	2004/09/09 10:32
S46	0	esd and threshold near (programming programmed programmable) near fuse	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 11:56
S47	8	esd near fuse	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 11:58
S48	42	esd same fuse same resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 14:10
S49	0	esd same fuse near resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 11:59
S50	15	"5,682,049"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 14:12
S51	4	("4786956" "4941028" "5341267" "5498895").PN.	USPAT	OR	ON	2004/09/09 14:28
S52	4	("4786956" "4941028" "5341267" "5498895").PN.	USPAT	OR	ON	2004/09/09 14:28
S53	13	"5682049".URPN.	USPAT	OR	ON	2004/09/09 14:30
S54	13	"5682049".URPN.	USPAT	OR	ON	2004/09/09 14:36
S55	74	"5,400,202"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 11:41

S56	27	"5,341,267"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 11:43
S57	2356	fuse near (programming programmable)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 11:43
S58	161	fuse near (programming programmable) same resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 11:44
S59	2	fuse near (programming programmable) same (resistor resistive) adj divider	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 12:00
S60	0	fuse near (resistor resistive) adj divider	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 12:01
S61	60	fuse same (resistor resistive) adj divider	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 12:02
S62	2	fuse same (resistor resistive) adj divider same programming	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 13:34
S63	8	("4417154" "4446534" "4480199" "4499387" "4533841" "4592025" "4593203" "4605872").PN.	USPAT	OR	ON	2004/09/10 13:34
S64	3919	361/56	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 15:04
S65	3	"6,365,938"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 15:49

S66	729	integrated near circuit and plasma near damage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 15:50
S67	7	integrated near circuit and plasma near damage near (protect protecting protection)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 15:54
S68	37	"5,760,445"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 15:54
S69	8	("5422507" "5519242" "5587598" "5682049" "5731600" "6060752" "6060753" "6091114").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/17 15:58
S70	0	("6365938").URPN.	USPAT	OR	OFF	2005/03/17 16:01
S71	0	("6365938").URPN.	USPAT	OR	OFF	2005/03/17 16:05
S72	8	("5422507" "5519242" "5587598" "5682049" "5731600" "6060752" "6060753" "6091114").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/17 16:05
S73	866	361/91.1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/17 16:33
S74	185	esd and (mos mosfet fet field adj effect) same (program programming programmed)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 09:24
S75	46	esd and (mos mosfet fet field adj effect) same (program programming programmed) and clamp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 09:24
S76	2250648	esd and (mos mosfet fet field adj effect) same (program programming programmed) and clamp and third (pad terminal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 09:24
S77	2	esd and (mos mosfet fet field adj effect) same (program programming programmed) and clamp and third near (pad terminal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 09:26

S78	11	esd and (mos mosfet fet field adj effect) same (program programming programmed) and third near (pad terminal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 09:28
S79	5	esd and (mos mosfet fet field adj effect) same (program programming programmed) near (pad terminal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 09:34
S80	0	overvoltage near (protectprotecting protectoin) and (mos mosfet fet field adj effect) same (program programming programmed) near (pad terminal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 09:34
S81	0	overvoltage near (protect protecting protectoin) and (mos mosfet fet field adj effect) same (program programming programmed) near (pad terminal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 09:34
S82	0	overvoltage near (protect protecting protection) and (mos mosfet fet field adj effect) same (program programming programmed) near (pad terminal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 09:35
S83	0	overvoltage and (mos mosfet fet field adj effect) same (program programming programmed) near (pad terminal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 09:35